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(71) Applicant (for all designated States except US): SEMI-  
CONDUCTOR ENERGY LABORATORY CO., LTD.  
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): YAMAZAKI,  
Shunpei [JP/JP]; c/o SEMICONDUCTOR ENERGY  
LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kana-  
gawa 2430036 (JP). MAEKAWA, Shinji [JP/JP]; c/o

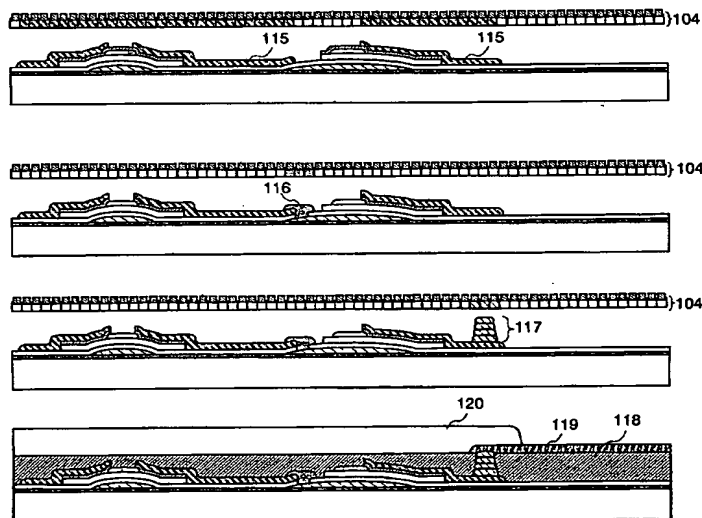
SEMICONDUCTOR ENERGY LABORATORY CO.,  
LTD., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).  
FUJII, Gen [JP/JP]; c/o SEMICONDUCTOR ENERGY  
LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kana-  
gawa 2430036 (JP). KUWABARA, Hideaki [JP/JP]; c/o  
SEMICONDUCTOR ENERGY LABORATORY CO.,  
LTD., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).  
TACHIMURA, Yuko [JP/JP]; c/o SEMICONDUCTOR  
ENERGY LABORATORY CO., LTD., 398, Hase, At-  
sugi-shi, Kanagawa 2430036 (JP).

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(54) Title: DISPLAY DEVICE AND METHOD FOR FABRICATING THE SAME



(57) Abstract: It is an object of the invention to provide a display device which can be manufactured by a simplified manufacturing process by which the efficiency in the use of material is improved. It is a further object of the invention to provide a manufacturing method of the display device. It is another object of the invention to provide a fabrication technology for improving adhesion of a pattern. In view of the above problems, according to the present invention, a pattern is formed by a droplet discharge method. Particularly in the invention, base pretreatment is performed before/after a pattern is formed by a droplet discharge method. As a result of such base pretreatment, adhesion of a pattern can be improved, and the pattern may be made finer.



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